

Specification Sheet

Boron Oxide Doped Silicon Wafer

Stock No: NS6130-10-1085, CAS: 7440-21-3

Product	:	Silicon Wafer 2"
Stock No	:	NS6130-10-1085
CAS	:	7440-21-3
Diameter	:	2"
Thickness	:	275 μ m
Dopant	:	Boron Oxide
Crystal Orientation	:	< 100>
Type	:	P
Growth Method	:	CZ
Resistivity	:	1.0-5.0 Ω .cm
TTV	:	< 10.0 μ m
STIR	:	< 2 μ m
GLOBAL TIR	:	< 5 μ m
Warp	:	< 50.0 μ m
LPD	:	< 30 counts @ particles size>0.3 μ m
Laser Mark	:	None
Edge Profile	:	Rounded
Front Surface	:	Polished
Back Surface	:	Etched
Bow	:	< 50.0 μ m
Main Inspect Verifier	:	Manager QC

Note: Product Specification are subject to amendment and may change over time

Characterization of Boron Oxide Doped Silicon Wafer



Boron Oxide Doped Silicon Wafer



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